

INITIAL PRODUCT/PROCESS CHANGE NOTIFICATION Generic Copy

13 May 2008

SUBJECT: ON Semiconductor Initial Product/Process Change Notification #16116

TITLE: Capacity Expansion Qualification of ON Semiconductor Gresham Wafer Fab for Devices Currently Fabricated at XFAB Wafer Foundries

PROPOSED FIRST SHIP DATE: 13 Sep 2008

AFFECTED CHANGE CATEGORY: ON Semi Fab Site / Subcontractor Fab Site

AFFECTED PRODUCT DIVISION: Digital Consumer Group, Computing Products Group

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Todd Manes todd.manes@onsemi.com>

NOTIFICATION TYPE:

Initial Product/Process Change Notification (IPCN)

First change notification sent to customers. IPCNs are issued at least 120 days prior to implementation of the change. An IPCN is advance notification about an upcoming change and contains general information regarding the change details and devices affected. It also contains the preliminary reliability qualification plan.

The completed qualification and characterization data will be included in the Final Product/Process Change Notification (FPCN).

This IPCN notification will be followed by a Final Product/Process Change Notification (FPCN) at least 90 days prior to implementation of the change.

DESCRIPTION AND PURPOSE:

ON Semiconductor is pleased to announce a capacity expansion qualification for devices currently fabricated at the XFAB wafer foundries.

Products currently qualified at the XFAB wafer foundry facilities (located in Erfurt, Germany and Lubbock, Texas) will now also be qualified at ON Semiconductor's Gresham wafer fabrication facility located in Gresham, Oregon. Upon expiration of the associated Final PCN(s), devices may be supplied from either the XFAB foundries or the Gresham fab.

The Gresham wafer fab is ISO9001:2000 compliant. The products currently run on XFAB's 0.6um BiCMOS process. Devices will be qualified to run at Gresham on the 0.25um "ONC25" process. Device performance will be the same among the qualified facilities for each device family. All devices will continue to be assembled and tested in existing, qualified locations. No changes to packaging will occur as a result of this foundry expansion qualification.

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QUALIFICATION PLAN:

Electrical Distribution

Full qualification testing will be performed as appropriate on each device family. Reliability testing may include the following (depending upon package and device-specific requirements):

Test High Temp Op Life (HTOL) High Temp Storage Life (HTSL) Early Life Failure Rate (ELFR) Pre-Conditioning (PC) PC + Autoclave(PC+AC)	Conditions 150C / 504 hrs 150C / 1000 hrs 150C/ 48 hrs MSL 1
for packaged parts PC + Highly Accelerated Stress Test (PC+HAST) PC + Unbiased HAST (PC+UHAST) PC + Temp Cycle (PC+TC)	121C/115psig / 96 hrs 131C/85%RH/96 hrs/Bias 130C/85%RH/96 hrs/No bias
for packaged parts for bumped parts	-65C/+150C/500 cyc -40C/+125C/500 cyc
ESD	Human Body Model / Machine Model
Latch Up PC + SAT Wire Bond Shear/ Bump Shear Wire Bond Pull	Dynamic Latch Up MSL 1 preconditioning AEC-Q100-001 AEC-Mil-Std-883 Meth 2011

Qualifications at the Gresham wafer fab will include a full set of reliability testing for the first devices to be qualified there. When sufficient qualification data has been gathered, future product qualifications will reuse qualification data as appropriate.

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AFFECTED DEVICE LIST:

PART

NCP1521ASNT1G

NCP1521BMUTBG

NCP1521BSNT1G

NCP1522BMUTBG

NCP1522BSNT1G

NCP1529ASNT1G

NCP1529MUTBG

NCP1532MUAATXG

NCP2820AFCT2G

NCP2820FCT1G

NCP2820FCT2G

NCP2820MUTBG

NCP2890AFCT2G

NCP2890DMR2G

NCP2892AFCT2G

NCP2892BFCT2G

NCP2990FCT2G

NCP4894DMR2G

NCP4894FCT1G

NCP4894MNR2G

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